



Description

The XPX90P04RD uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

 $V_{DS} = -40V I_{D} = -80 A$

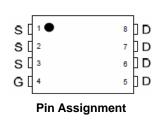
 $R_{DS(ON)} < 7m\Omega$ @ V_{GS} =-10V

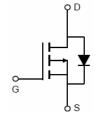
Application

Battery protection

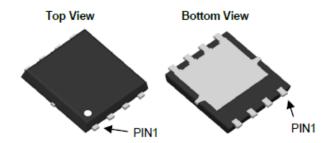
Load switch

Uninterruptible power supply





Schematic diagram



Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
XPX90P04RD	PDFN5*6-8L	XPX90P04	5000

Absolute Maximum Ratings (TC=25°C unless otherwise noted)

Symbol	Parameter	Rating	Units	
V _D s	Drain-Source Voltage	-40	V	
Vgs	Gate-Source Voltage	±20	V	
I _D @T _C =25°C	Continuous Drain Current, V _{GS} @ -10V ¹	-90	А	
I _D @T _C =100°C	Continuous Drain Current, V _{GS} @ -10V ¹	-56	Α	
Ірм	Pulsed Drain Current ²	-280	А	
EAS	Single Pulse Avalanche Energy ³	500	mJ	
las	Avalanche Current	-50	А	
P _D @T _C =25°C	Total Power Dissipation ⁴	52.1	W	
Тѕтс	Storage Temperature Range	-55 to 150	°C	
TJ	Operating Junction Temperature Range	-55 to 150	°C	
R_{θ} JA	Thermal Resistance Junction-Ambient ¹	25	°C/W	
Rejc	Thermal Resistance Junction-Case ¹	2.4	°C/W	





Electrical Characteristics (T_J=25℃, unless otherwise noted)

Symbol	Parameter	Conditions		Тур.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =-250uA	-40	-44		V
△BVdss/△TJ	BV _{DSS} Temperature Coefficient	Reference to 25°C , I _D =-1mA		-0.023		V/°C
_	Static Drain-Source On-Resistance ²	V _{GS} =-10V , I _D =-12A		7.0	10	
Rds(on)		V _{GS} =-4.5V , I _D =-12A		9.0	15	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250uA	-1.2	-1.8	-2.5	V
Ipss	Drain-Source Leakage Current	V _{DS} =-40V , V _{GS} =0V , T _J =25°C			1	uA
IDSS		V _{DS} =-40V , V _{GS} =0V , T _J =55°C			5	
Igss	Gate-Source Leakage Current	V _{GS} =±20V , V _{DS} =0V			±100	nA
gfs	Forward Transconductance	V _{DS} =-15V , I _D =-12A	-	20		S
Rg	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz		7	14	Ω
Q_g	Total Gate Charge (-4.5V)			27.9		
Qgs	Gate-Source Charge	V _{DS} =-20V , V _{GS} =-10V , I _D =-12A		7.7		nC
Qgd	Gate-Drain Charge	.5 .=	-	7.5		
Td(on)	Turn-On Delay Time			40		
Tr	Rise Time	V_{DD} =-20V , V_{GS} =-10V , R_{G} =3.0 Ω .		35.2		no
Td(off)	Turn-Off Delay Time	I _D =-12A	-	100		ns
T _f	Fall Time			9.6		
Ciss	Input Capacitance			6500		
Coss	Output Capacitance	V _{DS} =-20V , V _{GS} =0V , f=1MHz		790		pF
Crss	Reverse Transfer Capacitance		-	605		
ls	Continuous Source Current ^{1,5}	V _G =V _D =0V , Force Current			-70	Α
Vsp	Diode Forward Voltage ²	V _{GS} =0V , I _S =-1A , T _J =25°C			-1.2	V

Note:

- 1. The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper.
- 2_{\times} The data tested by pulsed , pulse width $\, \leqq \, 300 \text{us}$, duty cycle $\, \leqq \, 2\%$
- 3 The EAS data shows Max. rating . The test condition is VDD=-32V,VGS=-10V,L=0.1mH,IAS=-50A
- 5. The data is theoretically the same as ID and IDM, in real applications, should be limited by total power dissipation.







Rdson On-Resistance(m 2)

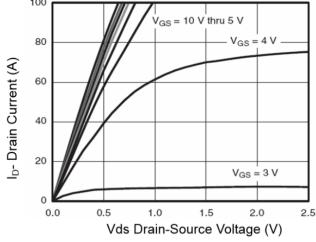


Figure 1 Output Characteristics

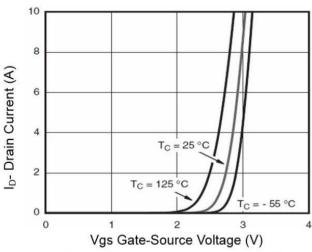


Figure 2 Transfer Characteristics

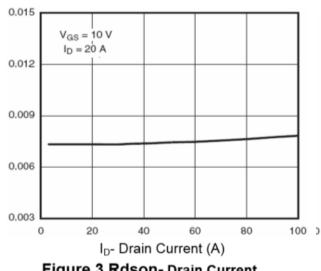


Figure 3 Rdson- Drain Current

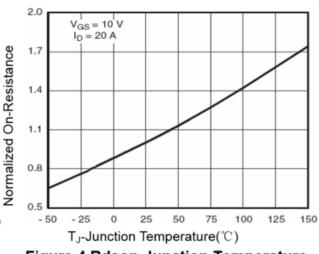


Figure 4 Rdson-Junction Temperature

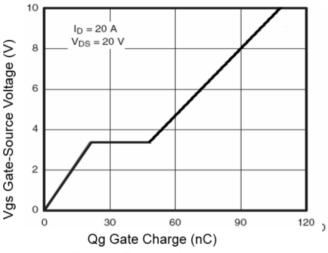


Figure 5 Gate Charge

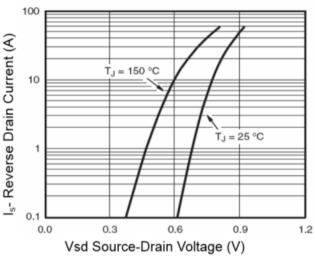


Figure 6 Source- Drain Diode Forward



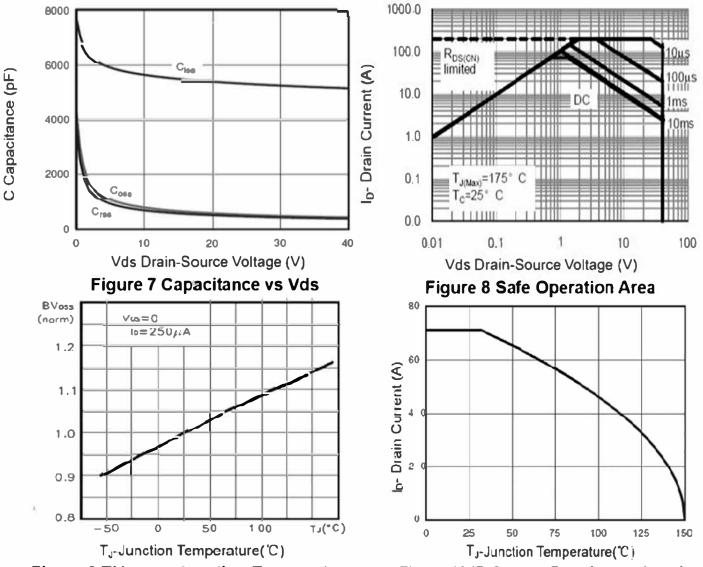


Figure 9 BV_{DSS} vs Junction Temperature

Figure 10 ID Current Derating vs Junction Temperature

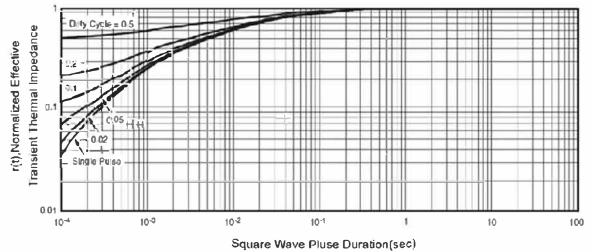
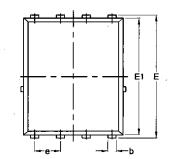
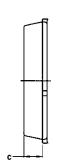


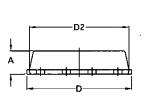
Figure 11 Normalized Maximum Transient Thermal Impedance

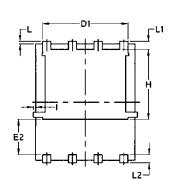


Package Mechanical Data-DFN5*6-8L-JQ Single









		Com	nmon	
Symbol	mm		In	ch
	Mim	Max	Min	Max
Α	1.03	1.17	0.0406	0.0461
b	0.34	0.48	0.0134	0.0189
С	0.824	0.0970	0.0324	0.082
D	4.80	5.40	0.1890	0.2126
D1	4.11	4.31	0.1618	0.1697
D2	4.80	5.00	0.1890	0.1969
E	5.95	6.15	0.2343	0.2421
E1	5.65	5.85	0.2224	0.2303
E2	1.60	/	0.0630	/
е	1.27 BSC		0.05	BSC
L	0.05	0.25	0.0020	0.0098
L1	0.38	0.50	0.0150	0.0197
L2	0.38	0.50	0.0150	0.0197
Н	3.30	3.50	0.1299	0.1378
	/	0.18	/	0.0070



Flow (wave) soldering (solder dipping)

Product	Peak Temperature	Dipping Time
Pb device	245℃±5℃	5sec±1sec
Pb-Free device	260℃+0/-5℃	5sec±1sec



This integrated circuit can be damaged by ESD UniverChip Corporation recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedure can cause damage. ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

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